

**MAXIMUM RATINGS:** ( $T_A=25^\circ\text{C}$ )

Continuous Reverse Voltage  
 Peak Repetitive Reverse Voltage  
 Continuous Forward Current  
 Peak Repetitive Forward Current  
 Forward Surge Current,  $t_p=1 \mu\text{sec}$ .  
 Forward Surge Current,  $t_p=1 \text{ sec}$ .  
 Power Dissipation  
 Operating and Storage  
 Junction Temperature  
 Thermal Resistance

**Central**<sup>TM</sup>  
**Semiconductor Corp.**

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CMXD6001 type contains three (3) Isolated Silicon Switching Diodes, manufactured by the epitaxial planar process, epoxy molded in a SUPERmini™ surface mount package, designed for switching applications requiring extremely low leakage.

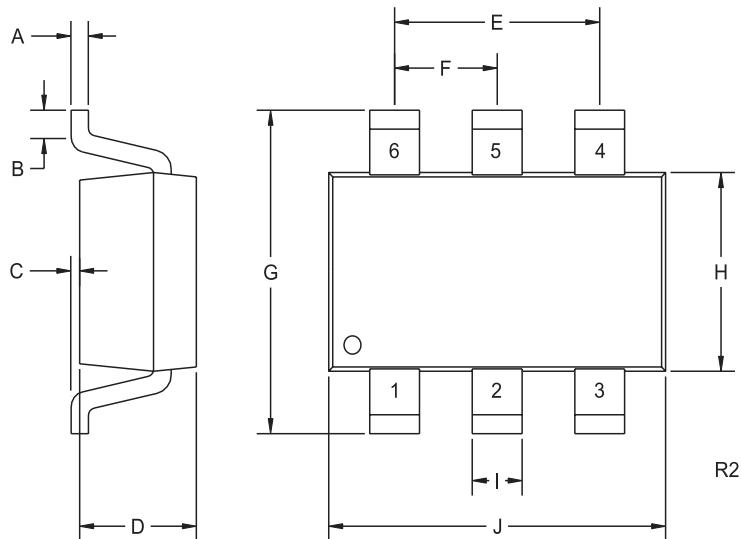
**MARKING CODE: X01**

SYMBOL	UNITS
$V_R$	V
$V_{RRM}$	V
$I_F$	mA
$I_{FRM}$	mA
$I_{FSM}$	mA
$I_{FSM}$	mA
$P_D$	mW
$T_J, T_{stg}$	${}^\circ\text{C}$
$\Theta_{JA}$	${}^\circ\text{C/W}$

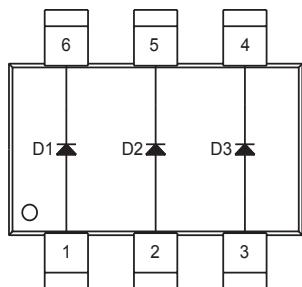
**ELECTRICAL CHARACTERISTICS PER DIODE:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
$I_R$	$V_R=75\text{V}$		500	pA
$BV_R$	$I_R=100\mu\text{A}$	100		V
$V_F$	$I_F=1.0\text{mA}$		0.85	V
$V_F$	$I_F=10\text{mA}$		0.95	V
$V_F$	$I_F=100\text{mA}$		1.1	V
$C_T$	$V_R=0, f=1 \text{ MHz}$		2.0	pF
$t_{rr}$	$I_R=I_F=10\text{mA}, R_L=100\Omega$ Rec. to 1.0mA		3.0	$\mu\text{s}$

SOT-26 CASE - MECHANICAL OUTLINE



**Pin Configuration**



SYMBOL	DIMENSIONS			
	INCHES	MILLIMETERS	MIN	MAX
A	0.004	0.007	0.11	0.19
B	0.016	-	0.40	-
C	-	0.004	-	0.10
D	0.039	0.047	1.00	1.20
E	0.074	0.075	1.88	1.92
F	0.037	0.038	0.93	0.97
G	0.102	0.118	2.60	3.00
H	0.059	0.067	1.50	1.70
I	0.016	-	0.41	-
J	0.110	0.118	2.80	3.00

SOT-26 (REV: R2)

**LEAD CODE**

- 1) ANODE D1
- 2) ANODE D2
- 3) ANODE D3
- 4) CATHODE D3
- 5) CATHODE D2
- 6) CATHODE D1

**MARKING CODE: X01**

R2 (6-August 2003)